



# STD1NK60 - STD1NK60-1 STQ1HNK60R - STN1HNK60

N-CHANNEL 600V - 8Ω - 1A DPAK/TO-92/IPAK/SOT-223  
SuperMESH™ MOSFET

**Table 1: General Features**

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STD1NK60	600 V	< 8.5 Ω	1 A	30 W
STD1NK60-1	600 V	< 8.5 Ω	1 A	30 W
STQ1HNK60R	600 V	< 8.5 Ω	0.4 A	3 W
STN1HNK60	600 V	< 8.5 Ω	0.4 A	3.3 W

- TYPICAL R<sub>DS(on)</sub> = 8 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- ESD IMPROVED CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

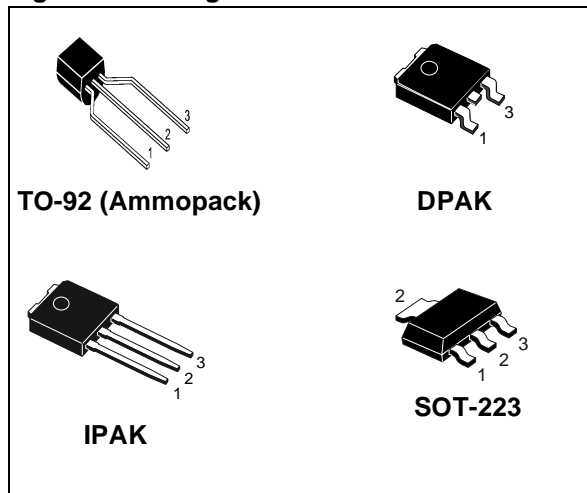
## DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

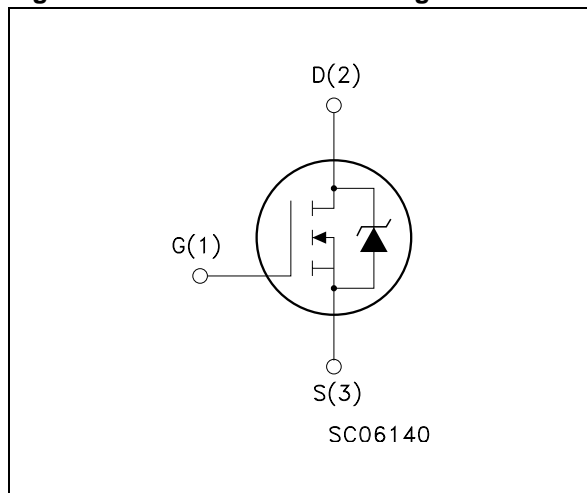
## APPLICATIONS

- LOW POWER BATTERY CHARGERS
- SWITCH MODE LOW POWER SUPPLIES(SMPS)
- LOW POWER, BALLAST, CFL (COMPACT FLUORESCENT LAMPS)

**Figure 1: Package**



**Figure 2: Internal Schematic Diagram**



**Table 2: Order Codes**

Part Number	Marking	Package	Packaging
STD1NK60T4	D1NK60	DPAK	TAPE & REEL
STD1NK60-1	D1NK60	IPAK	TUBE
STQ1HNK60R	1HNK60R	TO-92	BULK
STQ1HNK60R-AP	1HNK60R	TO-92	AMMOPAK
STN1HNK60	1HNK60	SOT-223	TAPE & REEL

Rev. 2

**Table 3: Absolute Maximum ratings**

Symbol	Parameter	Value			Unit
		DPAK / IPAK	TO-92	SOT-223	
$V_{DS}$	Drain-source Voltage ( $V_{GS} = 0$ )	600			V
$V_{DGR}$	Drain-gate Voltage ( $R_{GS} = 20\text{ k}\Omega$ )	600			V
$V_{GS}$	Gate- source Voltage	$\pm 30$			V
$I_D$	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	1.0	0.4	0.4	A
$I_D$	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	0.63	0.25	0.25	A
$I_{DM}(\bullet)$	Drain Current (pulsed)	4	1.6	1.6	A
$P_{TOT}$	Total Dissipation at $T_C = 25^\circ\text{C}$	30	3	3.3	W
	Derating Factor	0.24	0.025	0.025	W/ $^\circ\text{C}$
dv/dt (1)	Peak Diode Recovery voltage slope	3			V/ns
$T_j$ $T_{stg}$	Operating Junction Temperature Storage Temperature	-55 to 150			$^\circ\text{C}$

( $\bullet$ ) Pulse width limited by safe operating area

(1)  $I_{SD} \leq 1.0\text{A}$ ,  $di/dt \leq 100\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_j \leq T_{JMAX}$ .

**Table 4: Thermal Data**

		DPAK/IPAK	TO-92	SOT-223	Unit
Rthj-case	Thermal Resistance Junction-case Max	4.16	--	--	$^\circ\text{C}/\text{W}$
Rthj-amb	Thermal Resistance Junction-ambient Max	100	120	37.87 (#)	$^\circ\text{C}/\text{W}$
Rthj-lead	Thermal Resistance Junction-lead Max	--	40	--	$^\circ\text{C}/\text{W}$
$T_l$	Maximum Lead Temperature For Soldering Purpose	275	260		$^\circ\text{C}$

(#) When mounted on FR-4 board of  $1\text{ in}^2$ , 2oz Cu,  $t < 10\text{ sec}$

**Table 5: Avalanche Characteristics**

Symbol	Parameter	Max Value	Unit
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max)	1	A
$E_{AS}$	Single Pulse Avalanche Energy (starting $T_j = 25^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	25	mJ

**ELECTRICAL CHARACTERISTICS ( $T_{CASE} = 25^\circ\text{C}$  UNLESS OTHERWISE SPECIFIED)**
**Table 6: On/Off**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1\text{mA}$ , $V_{GS} = 0$	600			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ , $T_C = 125^\circ\text{C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body Leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 30\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	2.25	3	3.7	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 0.5\text{ A}$		8	8.5	$\Omega$

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**Table 7: Dynamic**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}$ (1)	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 0.5\text{ A}$		1		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$		156 23.5 3.8		pF pF pF
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time	$V_{DD} = 300\text{ V}, I_D = 0.5\text{ A},$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 21)		6.5 5 19 25		ns ns ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 4.7\ \Omega$ (see, Figure 23)		7 1.1 3.7	10	nC nC nC

**Table 8: Source Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}$ (2)	Source-drain Current Source-drain Current (pulsed)				1 4	A A
$V_{SD}$ (1)	Forward On Voltage	$I_{SD} = 1.0\text{ A}, V_{GS} = 0$			1.6	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}, T_j = 25^\circ\text{C}$ (see test circuit, Figure 22)		140 240 3.3		ns $\mu\text{C}$ A
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}, T_j = 150^\circ\text{C}$ (see test circuit, Figure 22)		229 377 3.3		ns $\mu\text{C}$ A

(1) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

(2) Pulse width limited by safe operating area.

Figure 3: Safe Operating Area For SOT-223

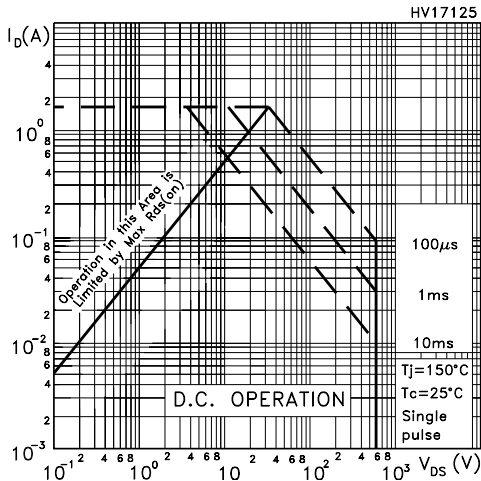


Figure 4: Safe Operating Area For DPAK/IPAK

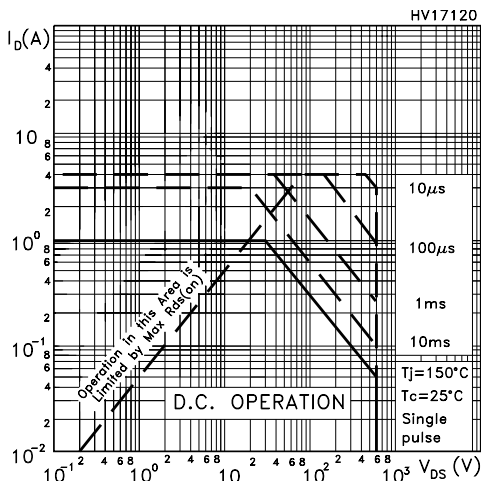


Figure 5: Safe Operating Area For TO-92

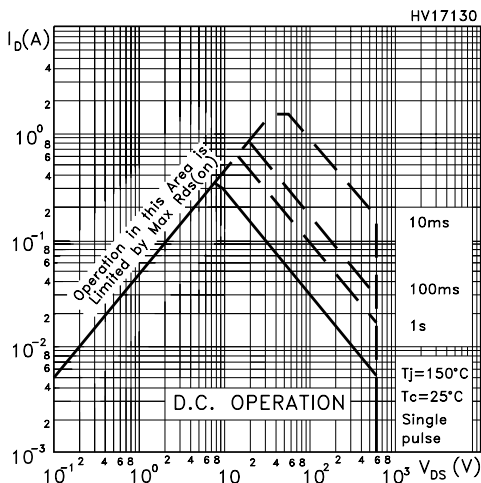


Figure 6: Thermal Impedance For SOT-223

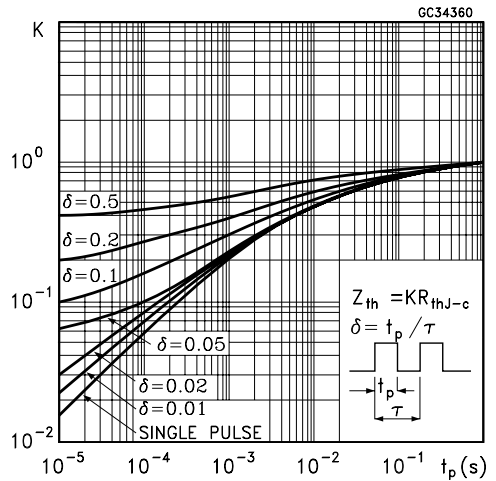


Figure 7: Thermal Impedance For DPAK/IPAK

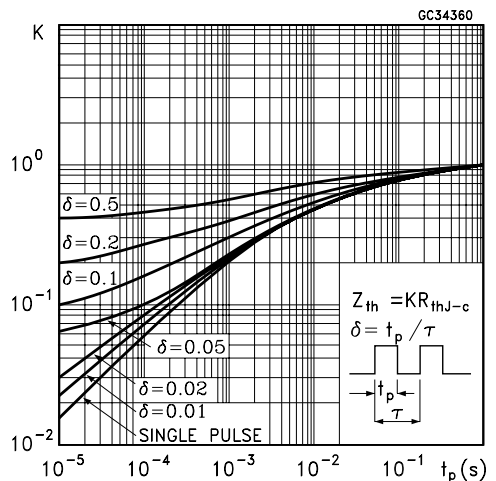


Figure 8: Thermal Impedance For TO-92

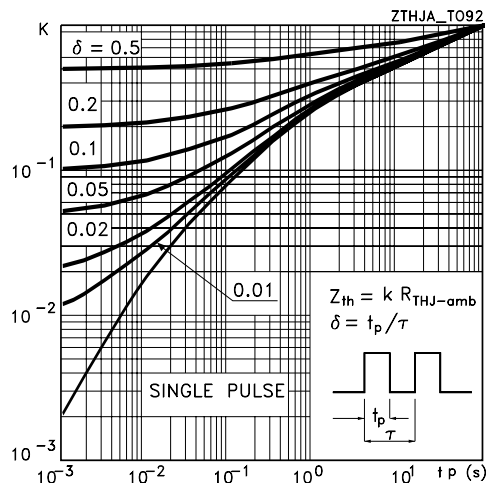


Figure 9: Output Characteristics

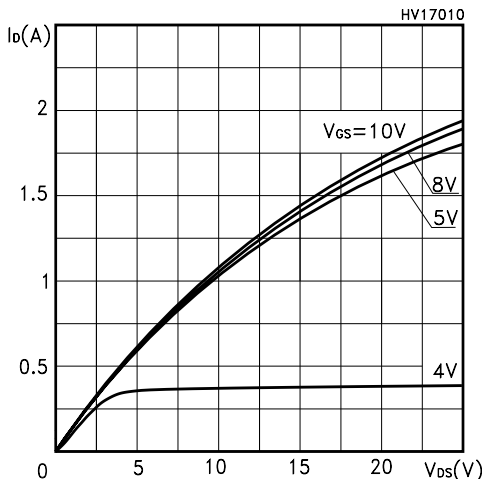


Figure 10: Transconductance

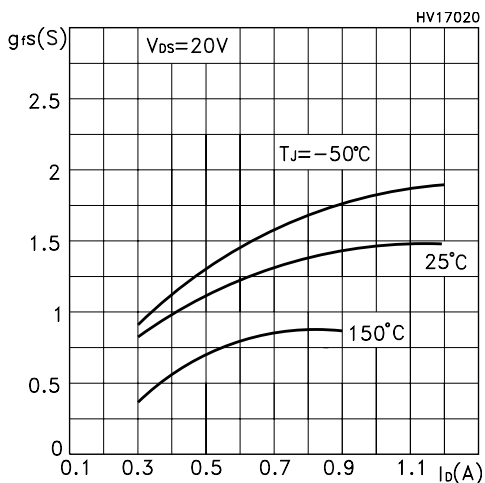


Figure 11: Capacitance Variations

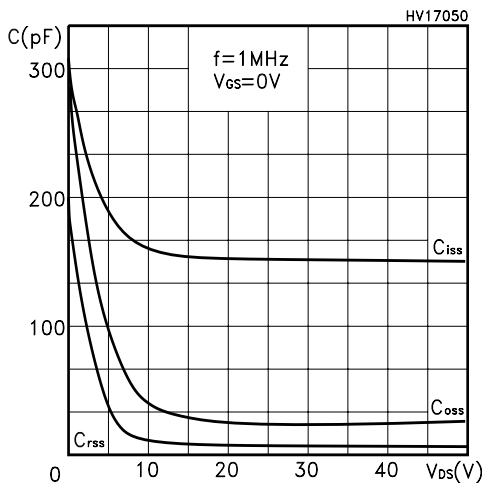


Figure 12: Transfer Characteristics

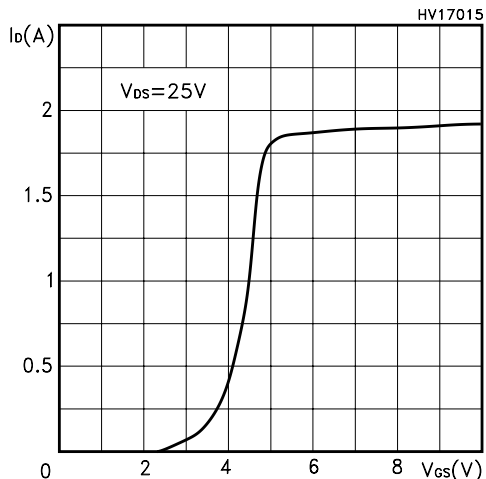


Figure 13: Gate Charge vs Gate-source Voltage

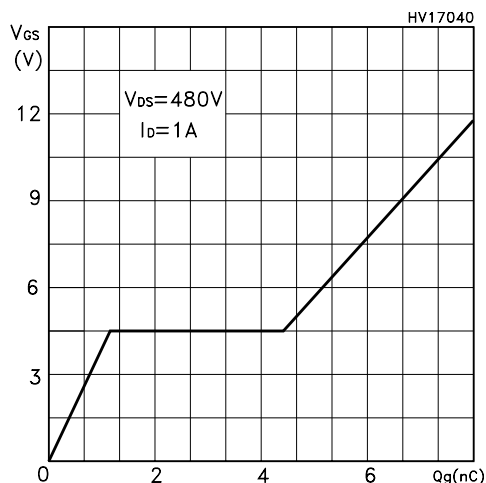


Figure 14: Static Drain-source On Resistance

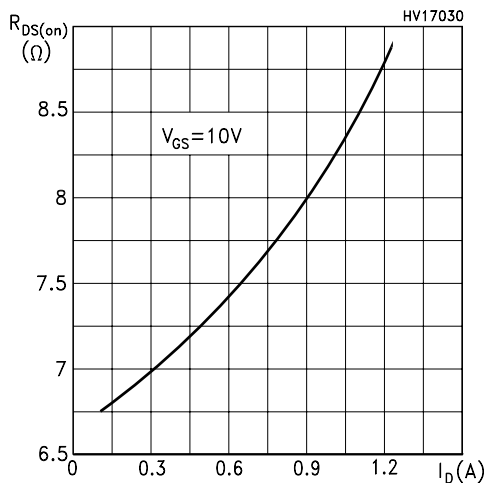


Figure 15: Normalized Gate Threshold Voltage vs Temperature

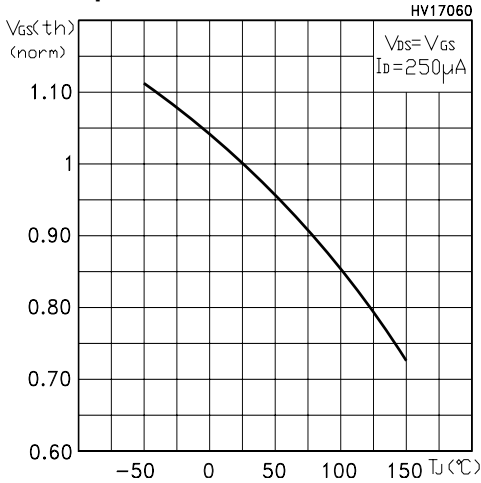


Figure 16: Source-Drain Forward Characteristics

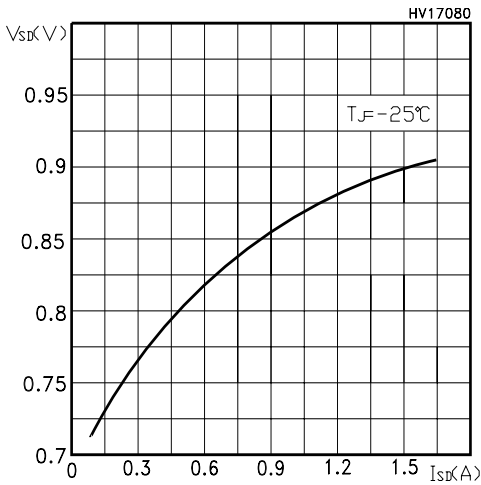


Figure 17: Maximum Avalanche Energy vs Temperature

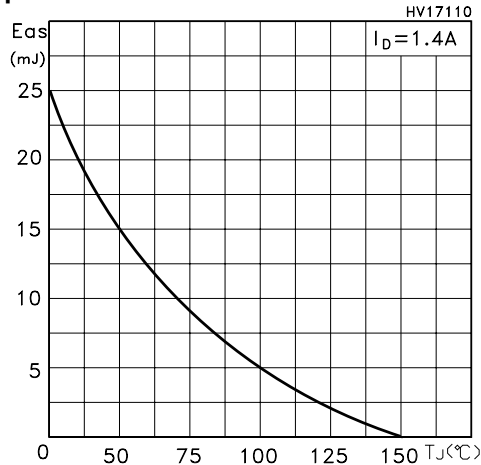


Figure 18: Normalized On Resistance vs Temperature

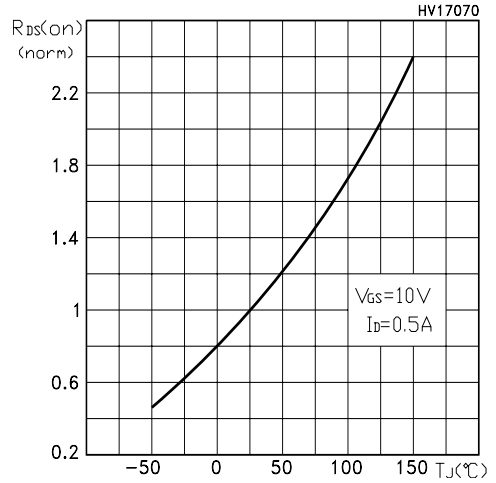


Figure 19: Normalized BV<sub>DSS</sub> vs Temperature

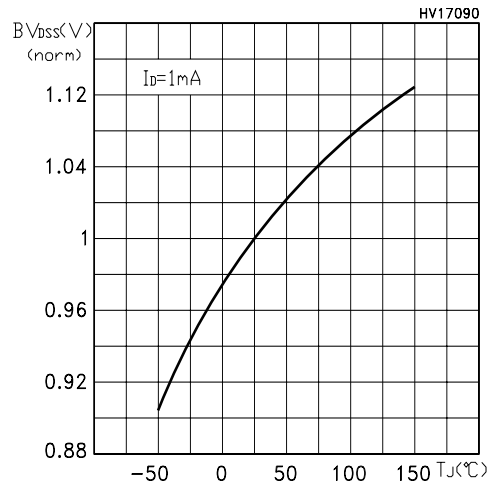


Figure 20: Max Id Current vs Tc

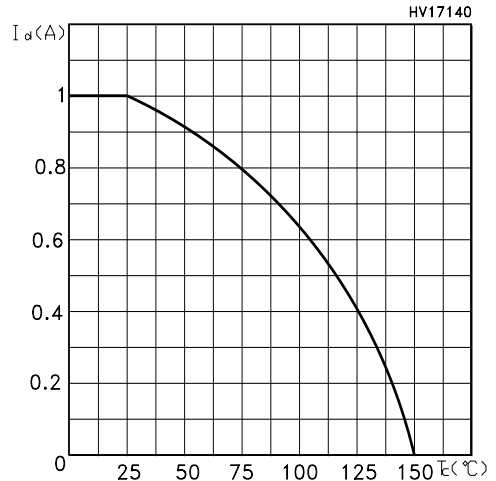


Figure 21: Switching Times Test Circuit For Resistive Load

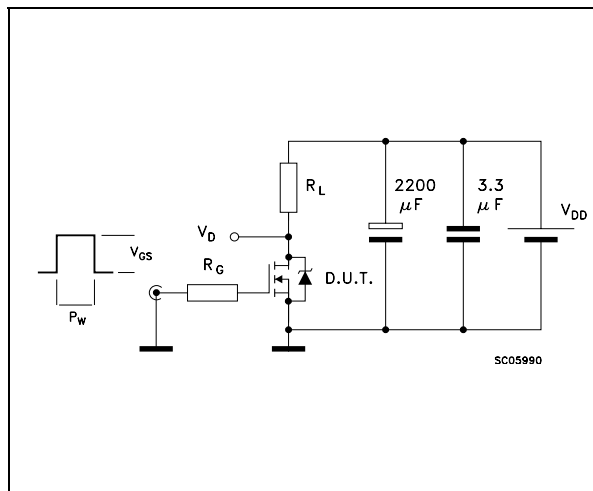


Figure 22: Test Circuit For Inductive Load Switching and Diode Recovery Times

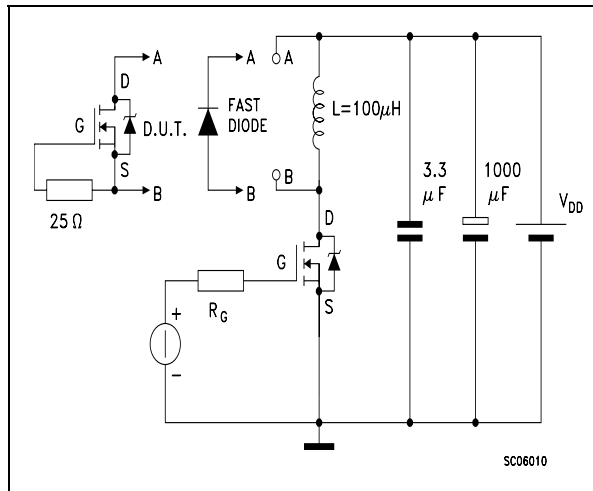
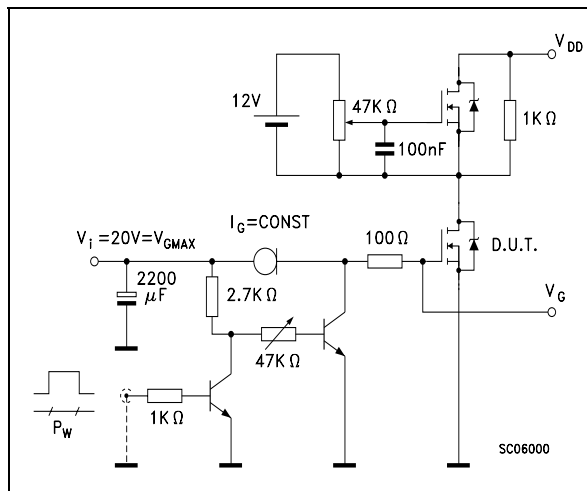
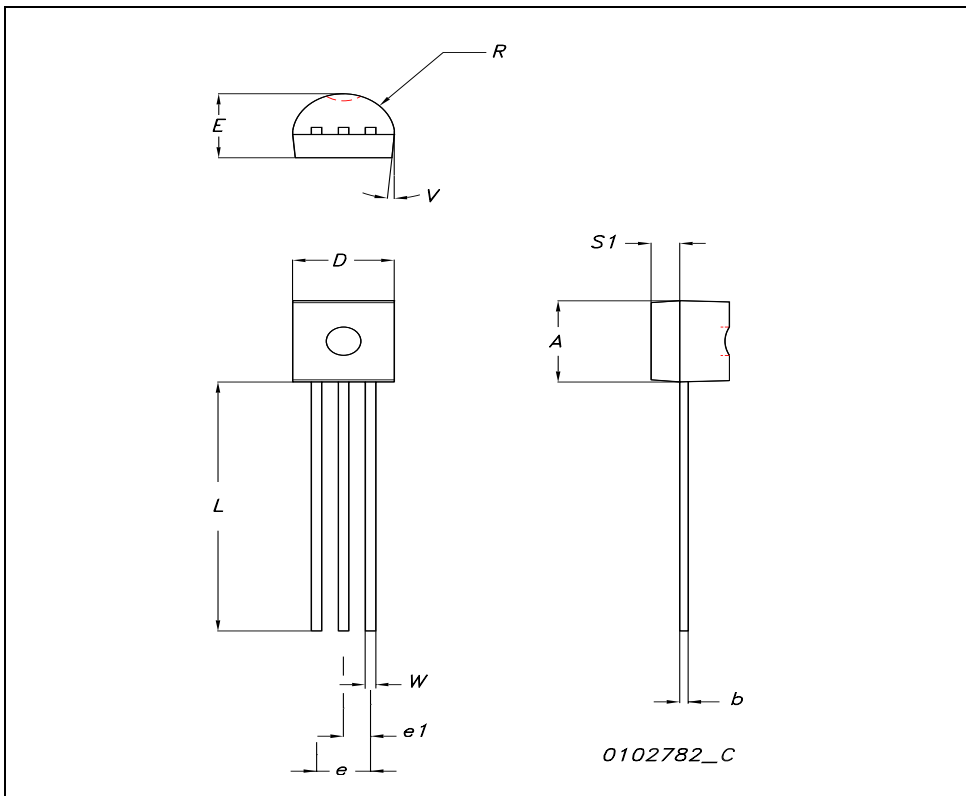


Figure 23: Gate Charge Test Circuit



**TO-92 MECHANICAL DATA**

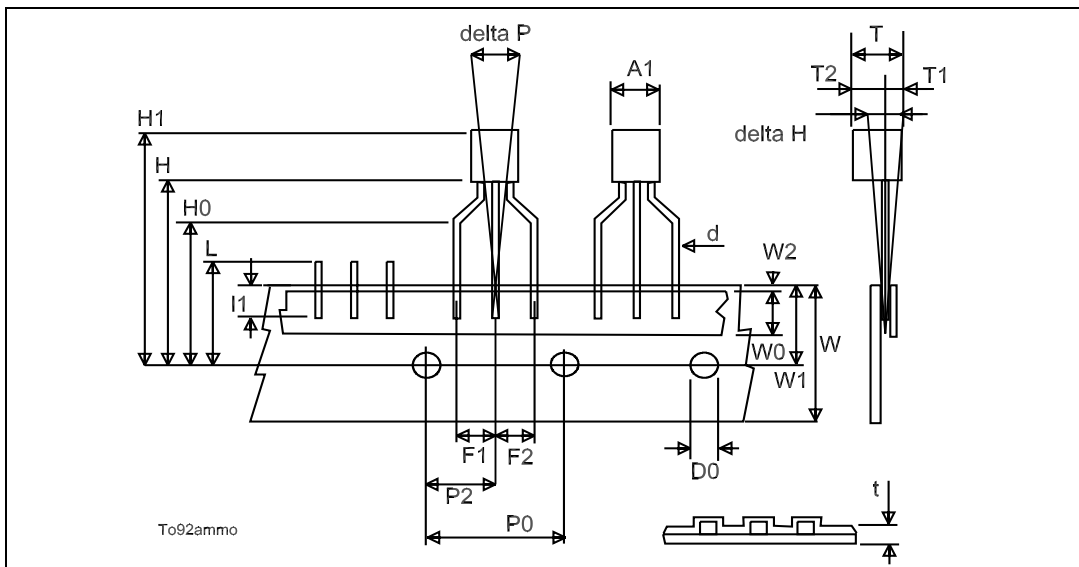
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.194
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.094		0.105
e1	1.14		1.40	0.044		0.055
L	12.70		15.49	0.50		0.610
R	2.16		2.41	0.085		0.094
S1	0.92		1.52	0.036		0.060
W	0.41		0.56	0.016		0.022
V		5°			5°	





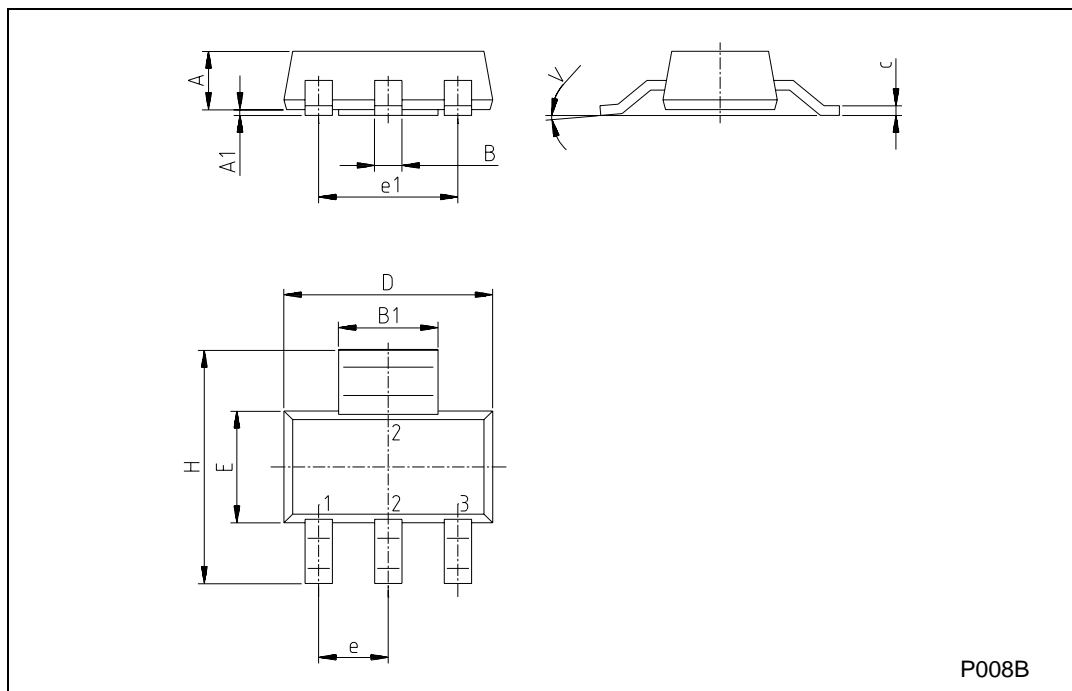
TO-92 AMMOPACK

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A1	4.45		4.95	0.170		0.194
T	3.30		3.94	0.130		0.155
T1			1.6			0.06
T2			2.3			0.09
d	0.41		0.56	0.016		0.022
P0	12.5	12.7	12.9	0.49	0.5	0.51
P2	5.65	6.35	7.05	0.22	0.25	0.27
F1, F2	2.44	2.54	2.94	0.09	0.1	0.11
delta H	-2		2	-0.08		0.08
W	17.5	18	19	0.69	0.71	0.74
W0	5.7	6	6.3	0.22	0.23	0.24
W1	8.5	9	9.25	0.33	0.35	0.36
W2			0.5			0.02
H	18.5		20.5	0.72		0.80
H0	15.5	16	16.5	0.61	0.63	0.65
H1			25			0.98
D0	3.8	4	4.2	0.15	0.157	0.16
t			0.9			0.035
L			11			0.43
l1	3			0.11		
delta P	-1		1	-0.04		0.04



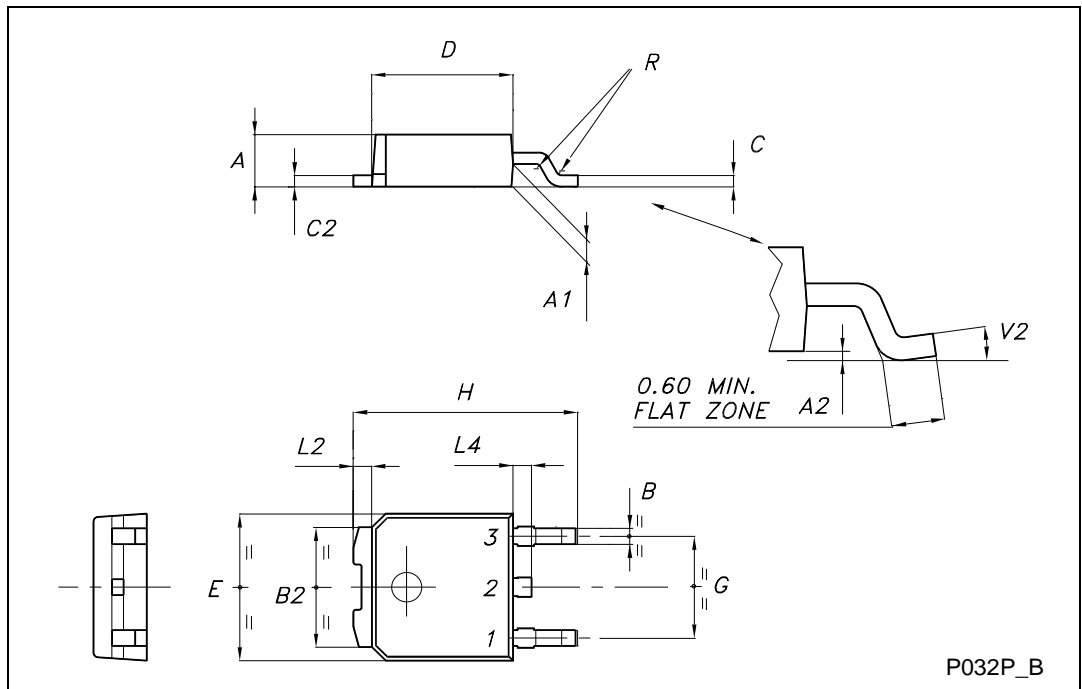
SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



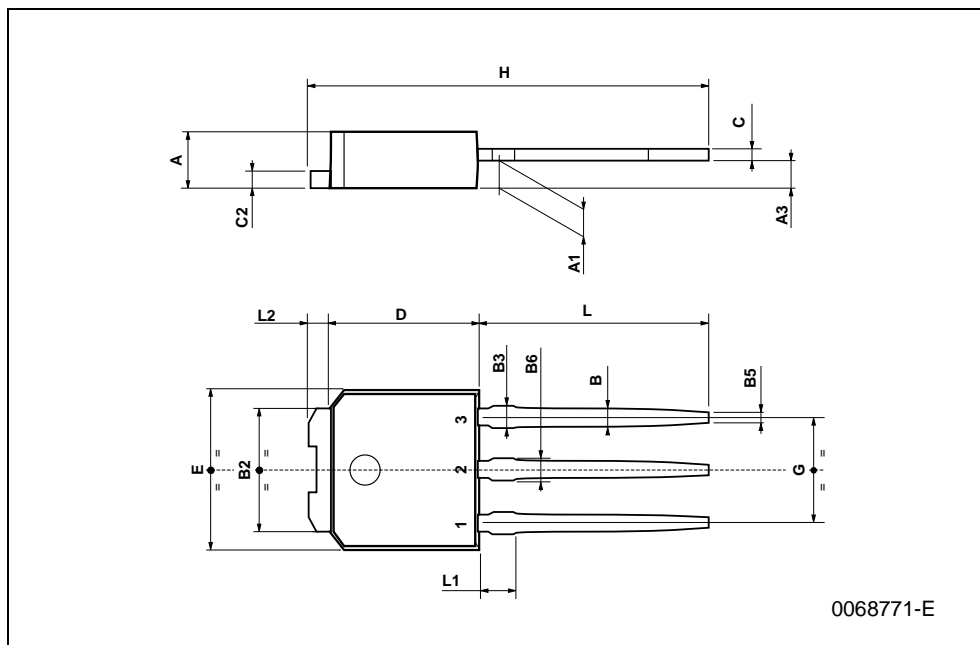
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



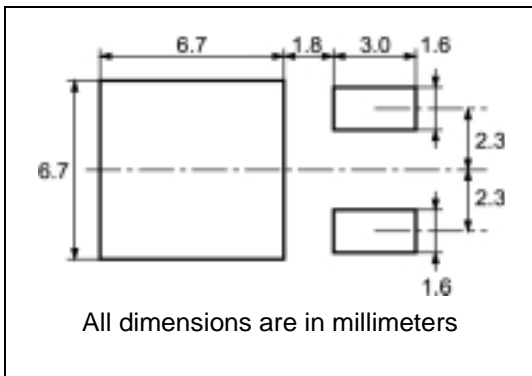
TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039

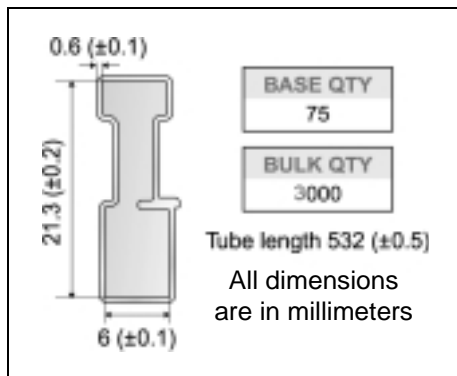


0068771-E

**DPAK FOOTPRINT**



**TUBE SHIPMENT (no suffix)\***



**TAPE AND REEL SHIPMENT (suffix "T4")\***

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

For machine mt. only including draft and radii concentric around DR

10 pitches cumulative tolerance on tape + / - 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

\* on sales type

**Table 9: Revision History**

<b>Date</b>	<b>Revision</b>	<b>Description of Changes</b>
22-Nov-2004	2	Added SOT-223 Package and new stylesheet

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

All other names are the property of their respective owners

© 2004 STMicroelectronics - All Rights Reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America